Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) Method for producing a lithium microbattery successively comprising formation of first and second current collectors ~~(2a, 2b)~~, of a cathode ~~(3)~~, of an electrolyte ~~(5)~~ comprising a lithiated compound and of an anode ~~(8)~~ comprising lithium on a substrate ~~(1), characterized in that~~

wherein the electrolyte formation step ~~of the electrolyte (5)~~ comprises at least the following successive operations:

deposition of an electrolytic thin layer ~~(5a)~~ on the substrate ~~(1)~~ provided with the current collectors ~~(2a, 2b)~~ and with the cathode ~~(3)~~,

deposition, on the electrolytic thin layer ~~(5a)~~, of a first protective thin layer ~~(6a)~~ that is chemically inert with regard to lithium, and then of a first masking thin layer ~~(7a)~~,

fabrication of a mask ~~(4d)~~ by photolithography on the first masking thin layer ~~(7a)~~,

selective etching of the first masking thin layer ~~(7a)~~ then removal of the mask ~~(4d)~~,

selective etching of the first protective thin layer ~~(6a)~~ and of the electrolytic thin layer ~~(5a)~~ so as to form the electrolyte ~~(5)~~ in the electrolytic thin layer ~~(5a)~~, and removal of the first protective thin layer ~~(6a)~~ and of the first masking thin layer ~~(7a)~~.

2. (Currently Amended) Method according to claim 1, ~~characterized in that~~wherein the first protective thin layer ~~(6a)~~ consists of a first material ~~chosen from a~~selected from the group consisting of a hydrogenated amorphous silicon carbide, a hydrogenated amorphous silicon oxycarbide, a hydrogenated amorphous silicon carbonitride, hydrogenated amorphous

carbon, fluorinated and hydrogenated amorphous carbon, a fluorinated and hydrogenated amorphous carbon nitride.

3. (Currently Amended) Method according to claim 2, ~~characterized in that~~wherein the first masking thin layer ~~(7a)~~ consists of a second material distinct from the first material and ~~chosen from a~~selected from the group consisting of a hydrogenated amorphous silicon carbide, a hydrogenated amorphous silicon oxycarbide, a hydrogenated amorphous silicon carbonitride, a silicon nitride and a silicon oxide.

4. (Currently Amended) Method according to ~~any one of the claims 1 to 3~~claim 1, ~~characterized in that~~wherein, once the electrolyte ~~(5a)~~ has been formed, a second protective thin layer ~~(6b)~~ is deposited on the whole of the substrate ~~(1)~~ comprising the current collectors ~~(2a, 2b)~~, the cathode ~~(3)~~ and the electrolyte ~~(5)~~.

5. (Currently Amended) Method according to claim 4, ~~characterized in that~~wherein the second protective thin layer ~~(6b)~~ consists of the same material as the first protective thin layer ~~(6a)~~.

6. (Currently Amended) Method according to ~~any one of the claims 1 to 5~~claim 1, ~~characterized in that~~wherein formation of the anode ~~(8)~~ comprises at least the following steps:

deposition of an anodic thin layer ~~(8a)~~ on the substrate ~~(1a)~~ provided with the current collectors ~~(2a, 2b)~~, the cathode ~~(3)~~ and the electrolyte ~~(5)~~,

deposition of a third protective thin layer ~~(6c)~~ and then of a second masking thin layer ~~(7b)~~ on the anodic thin layer ~~(5a)~~,

fabrication of a mask ~~(4c)~~ by photolithography on the second masking thin layer ~~(7b)~~,

selective etching of the second masking thin layer ~~(7b)~~ then removal of the mask ~~(4e)~~,

selective etching of the third protective thin layer ~~(6c)~~ and of the anodic thin layer ~~(8a)~~ so as to form the anode ~~(8)~~ in the anodic thin layer ~~(8a)~~ and removal of the third protective thin layer ~~(6c)~~ and the second masking thin layer ~~(7b)~~.

7. (Currently Amended) Method according to claim 6, ~~characterized in that~~wherein the third protective thin layer ~~(6c)~~ consists of the same material as the first protective thin layer ~~(6a)~~ whereas the second masking thin layer ~~(7b)~~ consists of the same material as the first masking thin layer ~~(7a)~~.

8. (Currently Amended) Method according to ~~any one of the claims 1 to 7~~claim 1, ~~characterized in that~~consisting, once the anode ~~(8)~~ has been formed, ~~it consists~~ in depositing a fourth protective layer ~~(6d)~~ on the stack formed by the current collectors ~~(2a, 2b)~~, the cathode ~~(3)~~, the electrolyte ~~(5)~~ and the anode ~~(8)~~.

9. (Currently Amended) Method according to claim 8, ~~characterized in that~~wherein the fourth protective thin layer ~~(6d)~~ consists of the same material as the first protective thin layer ~~(6a)~~.

10. (Currently Amended) Method according to ~~any one of the claims 1 to 7~~claim 1, ~~characterized in that~~consisting, once the anode ~~(8)~~ has been formed, ~~it consists~~ in depositing, on the stack formed by the current collectors ~~(2a, 2b)~~, the cathode ~~(3)~~, the electrolyte ~~(5)~~ and the anode ~~(8)~~, a protective envelope ~~(9)~~ covering the whole of the stack to protect the latter against any external contamination.

11. (Currently Amended) Method according to claim 10, ~~characterized in that~~wherein the protective envelope ~~(9)~~ comprising at least first and second distinct superposed encapsulation layers ~~(9a, 9b),~~and wherein the first encapsulation layer ~~(9a)~~ comprises at least one material that is chemically inert with regard to lithium, ~~chosen from a~~selected from the group consisting of a hydrogenated amorphous silicon carbide, a hydrogenated amorphous silicon oxycarbide, hydrogenated amorphous carbon, fluorinated amorphous carbon and hydrogenated amorphous silicon whereas the second encapsulation layer ~~(9b)~~ comprises a material ~~chosen from a~~selected from the group consisting of a hydrogenated amorphous silicon carbonitride, a hydrogenated amorphous silicon nitride and fluorinated amorphous carbon, the first and second encapsulation layers ~~(9a, 9b)~~ being successively deposited on the whole of the anode ~~(8)~~ by plasma enhanced chemical vapor deposition at a deposition temperature less than or equal to 150°C.

12. (Currently Amended) Method according to claim 11, ~~characterized in that it consists~~consisting, before deposition of the second encapsulation layer ~~(9b)~~, in depositing an intermediate layer ~~(9c)~~ comprising a material ~~chosen from a~~selected from the group consisting of a phosphorus-doped silicon oxide, hydrogenated amorphous carbon and fluorinated amorphous carbon by plasma enhanced chemical vapor deposition at a deposition temperature less than or equal to 150°C.